

ABSTRACT OF THE DISCLOSURE

A thin film transistor. The thin film transistor has an ultra thin polysilicon layer over a substrate, a gate structure that includes a gate layer, a gate oxide layer between the gate layer and the ultra thin polysilicon layer and a spacer on each sidewall
5 of the gate layer, and a conductive layer over the ultra thin polysilicon layer and the gate layer adjacent to the spacers. A selective deposition, such as an in-situ silicon-germanium deposition that utilizes the difference in properties between the spacer and silicon, is conducted to form the conductive layer.